

REMARKS

This application is a divisional application of U.S. Patent Application Serial No. 10/300,175. Original claims 1-26 have been cancelled without prejudice. New claims 27-37 are in the application for consideration.

In the drawings, Figs. 5-7 have been amended to correct minor typographical errors. No new matter is being introduced by way of this amendment.

Claim 27 recites, in part, a static random access memory cell comprising first and second inverters comprising a doped active area common to the drains of the first conductivity type transistors and a contiguous region in the substrate extending from the drain of one of the first conductivity type transistors to the drain of the other of the first conductivity type transistor. Such claimed subject matter was indicated to be allowable on page 2 of the parent application having Serial No. 10/300,175. Claim 27 is therefore allowable.

As claims 28-31 depend on claim 27, they too are in allowable.

Claim 32 includes subject matter indicated to be allowable for claim 45 of the parent application having Serial No. 10/300,175. Claim 32 is therefore allowable.

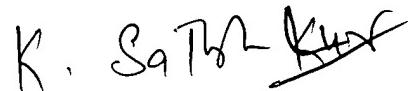
As claims 33-37 depend from claim 32, they too are allowable.

This application is believed to be in immediate condition for allowance,
and action to that end is requested.

Respectfully submitted,

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By:



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